

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

ATP204 — General-Purpose Switching Device Applications

Features

- · Low ON-resistance
- 4.5V drive
- · Halogen free compliance

- · Large current
- · Slim package
- · Protection diode in

Specifications

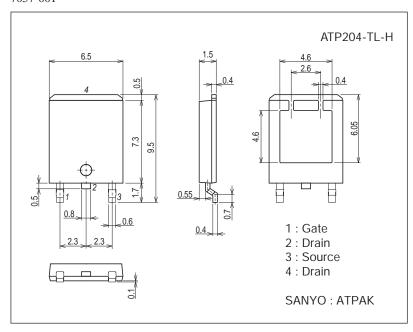
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		100	Α
Drain Current (PW≤10μs)	IDP	PW≤10μs, duty cycle≤1%	300	Α
Allowable Power Dissipation	PD	Tc=25°C	60	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		235	mJ
Avalanche Current *2	I _{AV}		50	А

Note: *1 V_{DD}=15V, L=100μH, I_{AV}=50A

Package Dimensions

unit : mm (typ) 7057-001



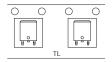
Product & Package Information

• Package : ATPAK

• JEITA, JEDEC : -

• Minimum Packing Quantity : 3,000 pcs./reel

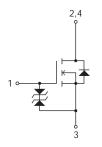
Packing Type: TL



Marking



Electrical Connection



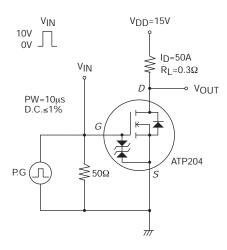
^{*2} L≤100μH, Single pulse

ATP204

Electrical Characteristics at Ta=25°C

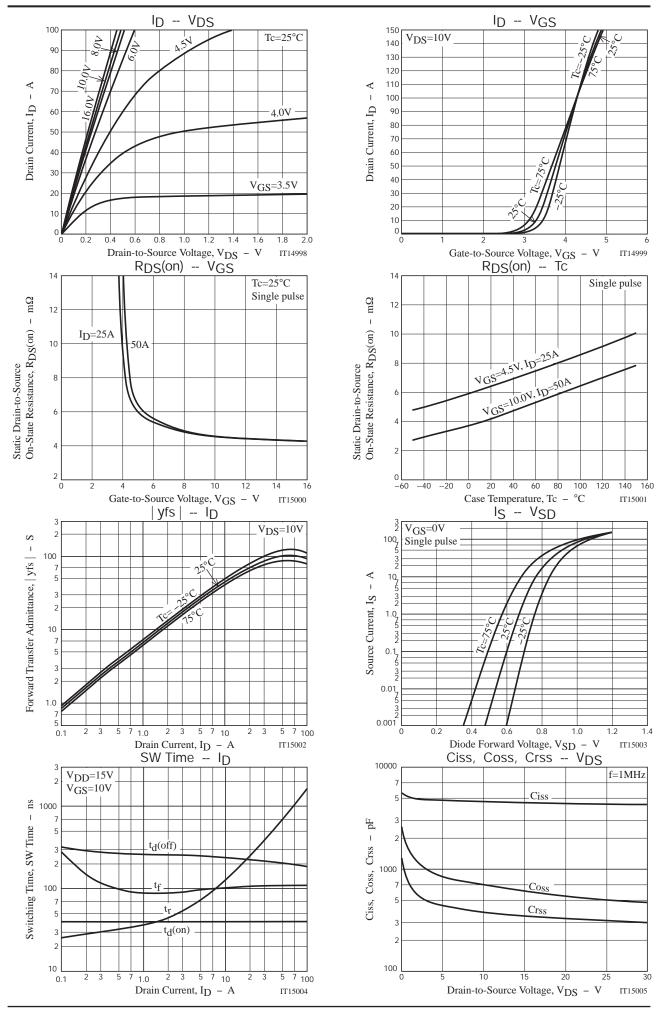
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Oniii	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	30			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.2		2.6	٧	
Forward Transfer Admittance	yfs	VDS=10V, ID=50A		100		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =50A, V _G S=10V		4.3	5.6	mΩ	
	R _{DS} (on)2	I _D =25A, V _G S=4.5V		6.5	9.1	mΩ	
Input Capacitance	Ciss			4600		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		700		pF	
Reverse Transfer Capacitance	Crss			390		pF	
Turn-ON Delay Time	t _d (on)			40		ns	
Rise Time	t _r	Sac appointed Toot Circuit		690		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		205		ns	
Fall Time	tf			110		ns	
Total Gate Charge	Qg			70		nC	
Gate-to-Source Charge	Qgs	V _{DS} =15V, V _{GS} =10V, I _D =100A		22		nC	
Gate-to-Drain "Miller" Charge	Qgd			9.2		nC	
Diode Forward Voltage	VSD	IS=100A, VGS=0V		1.03	1.2	V	

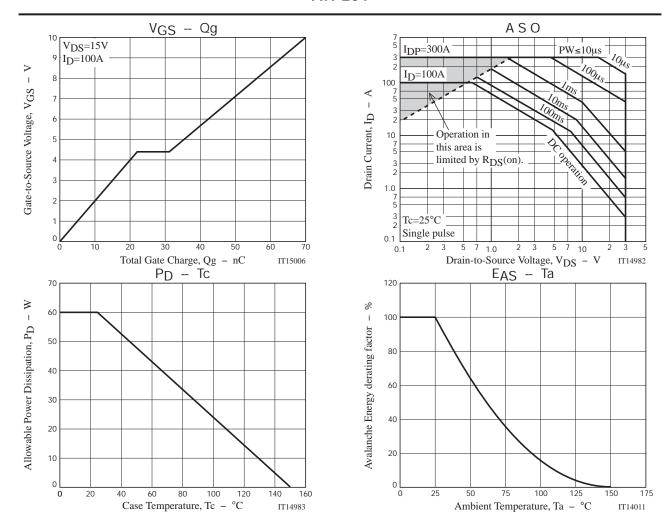
Switching Time Test Circuit



Ordering Information

Device	Device Package		memo	
ATP204-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free	



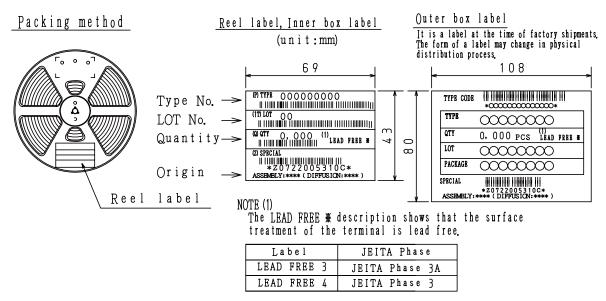


Taping Specification

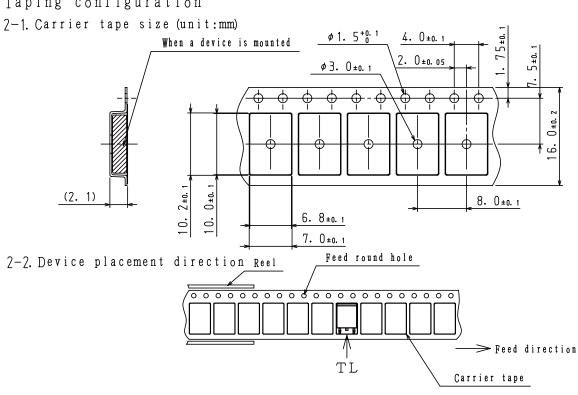
ATP204-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
Lacyake Mame	Туре	Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18	
					1 reels contained	5 inner boxes contained	
ATPAK ATP	3,000 3,00	3,000	10 15,000	Dimensions:mm (external)	Dimensions:mm (external)		
					340×340×28	355×355×165	



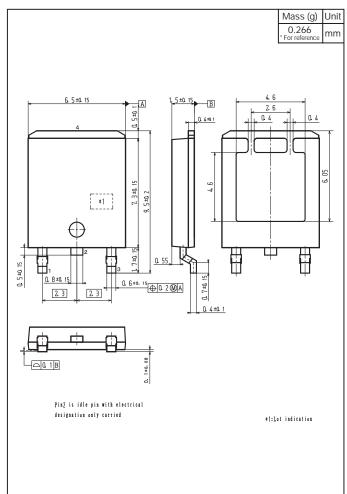
7. Taping configuration



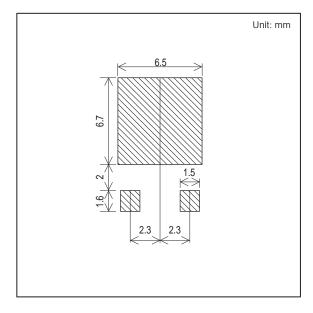
The one erectrode terminals on feed hole side····TL

Outline Drawing

ATP204-TL-H



Land Pattern Example



Note on usage: Since the ATP204 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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